

# **HVM187WK**

## Silicon Epitaxial Planar Pin Diode for High Frequency Attenuator

REJ03G0116-0600Z (Previous: ADE-208-056E) Rev.6.00

Oct.08.2003

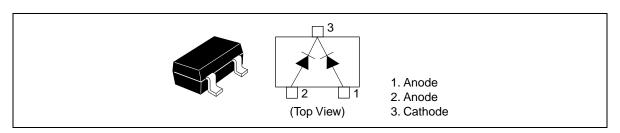
#### **Features**

- Low forward resistance. ( $r_f = 5.5 \Omega \text{ max}$ )
- MPAK package is suitable for high density surface mounting and high speed assembly.

### **Ordering Information**

Type No.	Laser Mark	Package Code	
HVM187WK	H1	MPAK	

### **Pin Arrangement**



### HVM187WK

### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit	
Reverse voltage	$V_R$	60	V	_
Forward current	I <sub>F</sub>	50	mA	
Power dissipation	Pd * <sup>1</sup>	100	mW	_
Junction temperature	Tj	125	°C	
Storage temperature	Tstg	−55 to +125	°C	

Note: 1. Per one device.

### **Electrical Characteristics** \*1

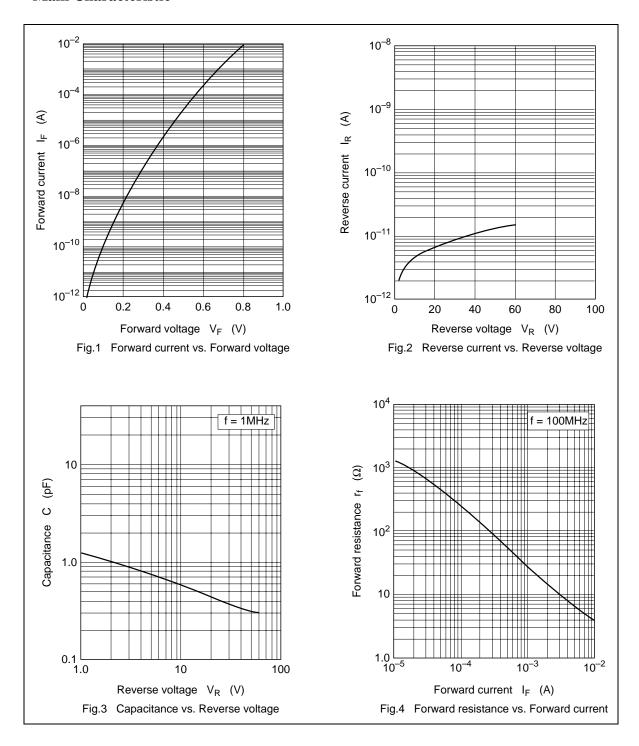
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse current	I <sub>R</sub>	_	_	100	nΑ	V <sub>R</sub> = 60 V
Forward voltage	V <sub>F</sub>	_	_	1.0	V	I <sub>F</sub> = 10 mA
Capacitance	С	_	_	2.4	pF	$V_R = 0 V, f = 1 MHz$
Forward resistance	r <sub>f</sub>	3.5	_	5.5	Ω	I <sub>F</sub> = 10 mA, f = 100 MHz
ESD-Capability *2	_	200	_	_	V	C = 200 pF, Both forward and reverse direction 1 pulse.

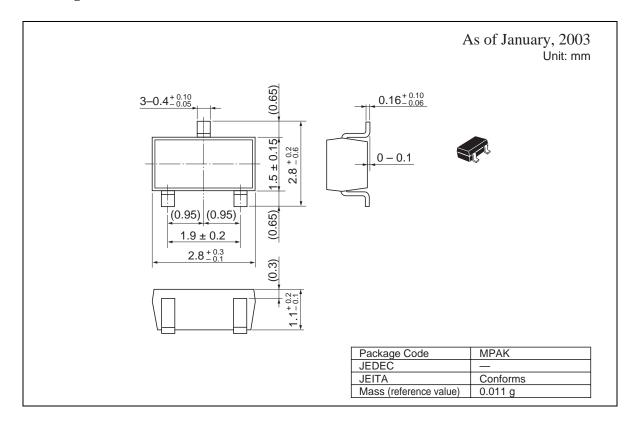
Notes: 1. Per one device.

2. Failure criterion ;  $I_R \geq 100 \; nA$  at  $V_R = 60 \; V$ 

### **Main Characteristic**



### **Package Dimensions**



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Renesas Technology Singapore Pte. Ltd.
1, Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

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